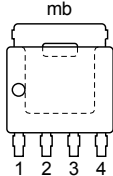
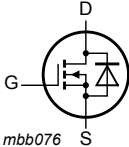


Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 10	1	1.44	1.9	mΩ
Dynamic characteristics						
Q <sub>GD</sub>	gate-drain charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 4.5 V; Fig. 12; Fig. 13	-	7.3	14.6	nC
Source-drain diode						
Q <sub>r</sub>	recovered charge	I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C; Fig. 16	-	26.8	-	nC
S	softness factor		-	0.85	-	

[1] 120A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 LFAK56; Power-SO8 (SOT669)	 mbb076
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9Y1R9-40H	LFAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9Y1R9-40H	91H940

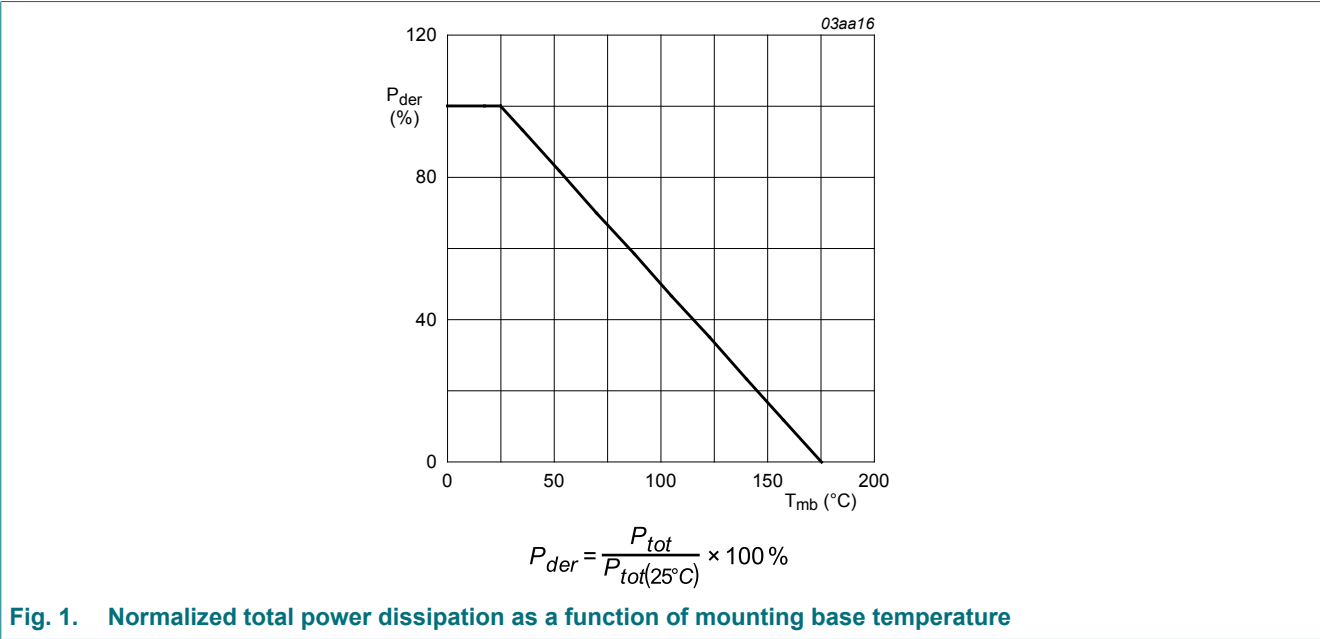
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	40	V
V <sub>GS</sub>	gate-source voltage	DC; T <sub>j</sub> ≤ 175 °C		-10	16	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; Fig. 1		-	217	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C	[1]	-	120	A
I <sub>DM</sub>	peak drain current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C; Fig. 2		-	600	A
T <sub>stg</sub>	storage temperature			-55	175	°C
T <sub>j</sub>	junction temperature			-55	175	°C
Source-drain diode						
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	120	A
I <sub>SM</sub>	peak source current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C		-	600	A
Avalanche ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	I <sub>D</sub> = 120 A; V <sub>sup</sub> ≤ 40 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; unclamped; Fig. 3	[2] [3]	-	108	mJ

- [1] 120A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C
- [3] Refer to application note AN10273 for further information



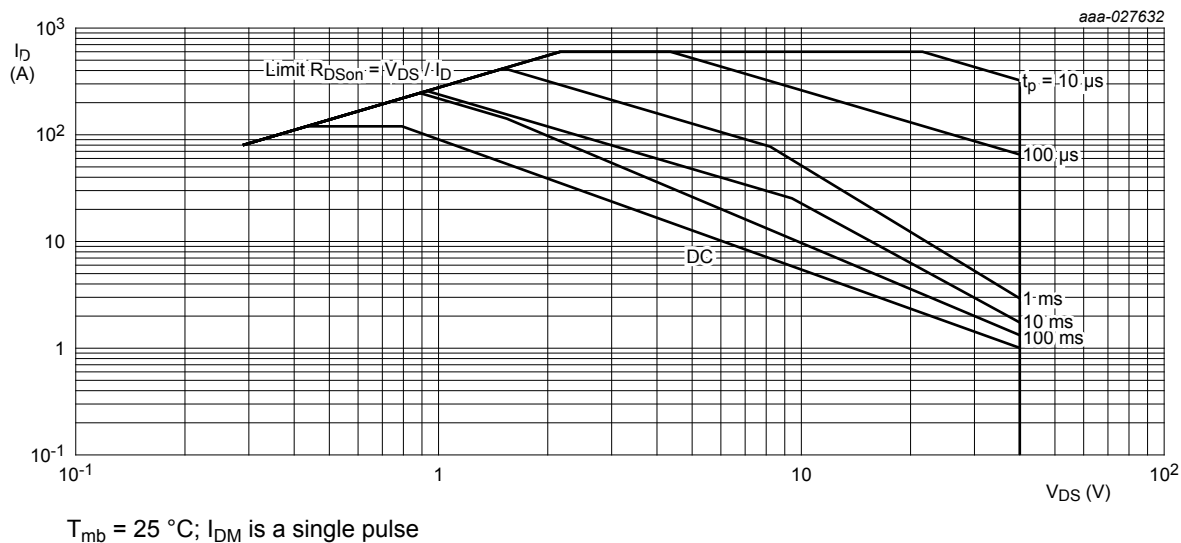
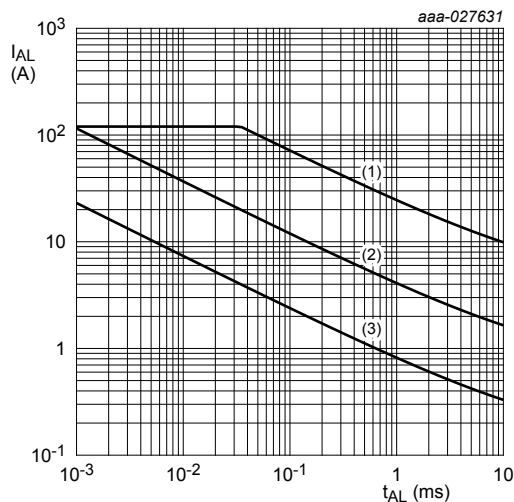


Fig. 2. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1)  $T_{j(init)} = 25^\circ\text{C}$ ; (2)  $T_{j(init)} = 150^\circ\text{C}$ ; (3) Repetitive Avalanche  
Fig. 3. Avalanche rating; avalanche current as a function of avalanche time

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 4	-	0.5	0.69	K/W

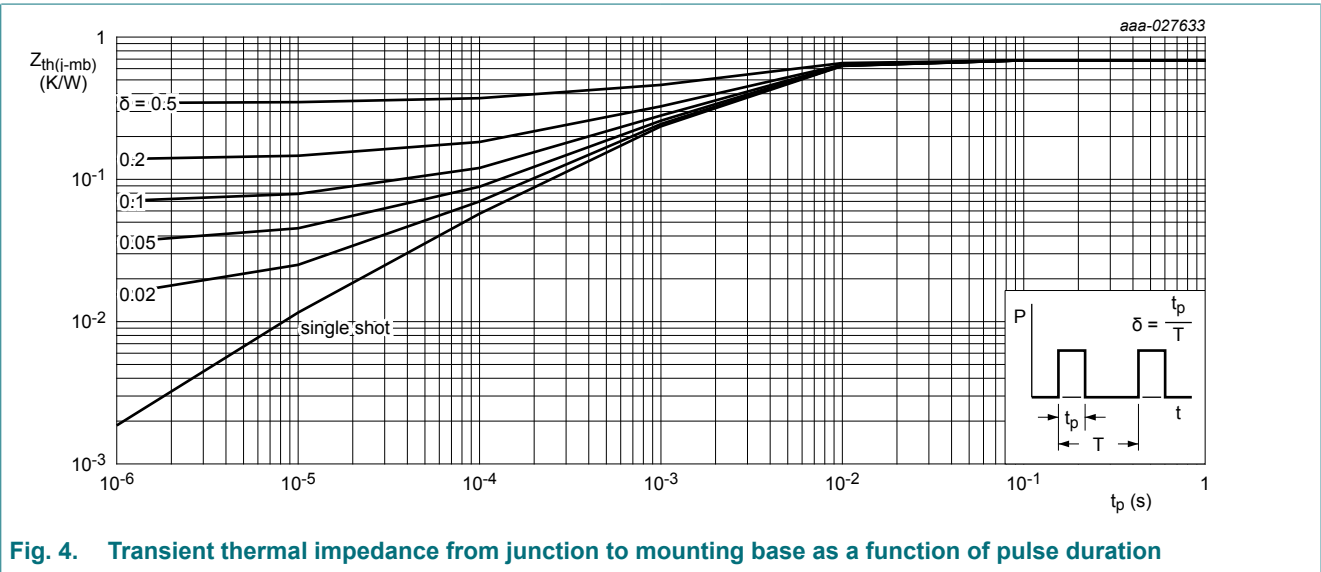


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 25 °C	40	43	-	V
		I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>J</sub> = -40 °C	-	40.5	-	V
		I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>J</sub> = -55 °C	36	40	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>J</sub> = 25 °C; Fig. 8; Fig. 9	1.35	1.66	2.05	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>J</sub> = 175 °C; Fig. 9	0.6	-	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>J</sub> = -55 °C; Fig. 9	-	-	2.5	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 25 °C	-	0.13	5	μA
		V <sub>DS</sub> = 16 V; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 125 °C	-	1.5	10	μA
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 175 °C	-	194	500	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>J</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>J</sub> = 25 °C	-	2	100	nA

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 25 °C; <a href="#">Fig. 10</a>		1	1.44	1.9	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 105 °C; <a href="#">Fig. 11</a>		1.5	2.2	3	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 125 °C; <a href="#">Fig. 11</a>		1.65	2.43	3.3	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 175 °C; <a href="#">Fig. 11</a>		2.1	3.06	4.2	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 25 °C; <a href="#">Fig. 10</a>		1.3	1.85	2.6	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 105 °C; <a href="#">Fig. 11</a>		1.9	2.8	4.1	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 125 °C; <a href="#">Fig. 11</a>		2.1	3.1	4.5	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 175 °C; <a href="#">Fig. 11</a>		2.7	3.9	5.7	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>J</sub> = 25 °C		0.32	0.8	2	Ω
<b>Dynamic characteristics</b>							
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 10 V; <a href="#">Fig. 12; Fig. 13</a>		-	66.4	93	nC
		I <sub>D</sub> = 25 A; V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 4.5 V; <a href="#">Fig. 12; Fig. 13</a>		-	30.4	42.7	nC
Q <sub>GS</sub>	gate-source charge			-	11	16.5	nC
Q <sub>GD</sub>	gate-drain charge			-	7.3	14.6	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>J</sub> = 25 °C; <a href="#">Fig. 14</a>		-	4665	6531	pF
C <sub>oss</sub>	output capacitance			-	960	1340	pF
C <sub>rss</sub>	reverse transfer capacitance			-	180	392	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 20 V; R <sub>L</sub> = 0.8 Ω; V <sub>GS</sub> = 4.5 V; R <sub>G(ext)</sub> = 5 Ω		-	26.5	-	ns
t <sub>r</sub>	rise time			-	30.6	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	33.5	-	ns
t <sub>f</sub>	fall time			-	20.5	-	ns
<b>Source-drain diode</b>							
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 25 °C; <a href="#">Fig. 15</a>		-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 20 V; T <sub>J</sub> = 25 °C; <a href="#">Fig. 16</a>		-	32.3	-	ns
Q <sub>r</sub>	recovered charge			-	26.8	-	nC
S	softness factor			-	0.85	-	
		I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -500 A/μs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 20 V; T <sub>J</sub> = 25 °C; <a href="#">Fig. 16</a>		-	0.7	-	

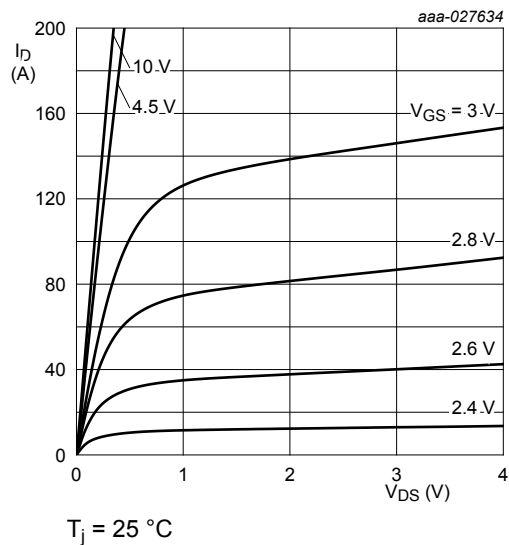


Fig. 5. Output characteristics; drain current as a function of drain-source voltage; typical values

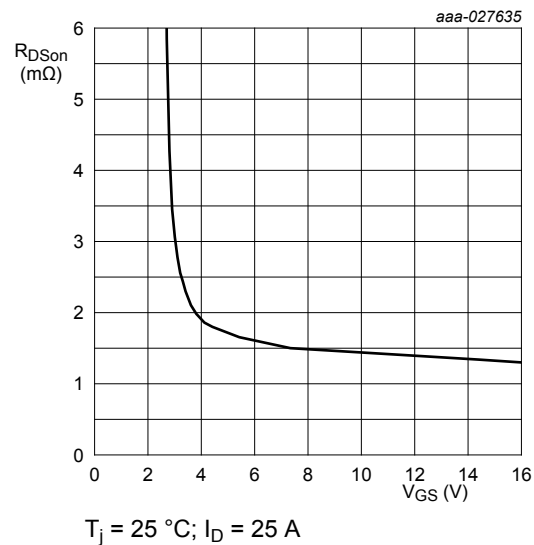


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

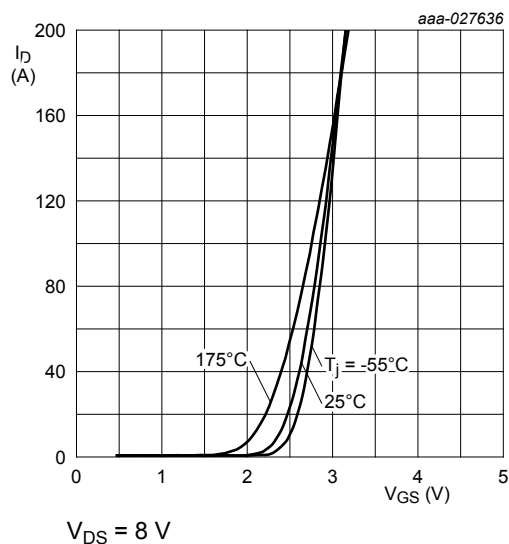


Fig. 7. Transfer characteristics; drain current as a function of gate-source voltage; typical values

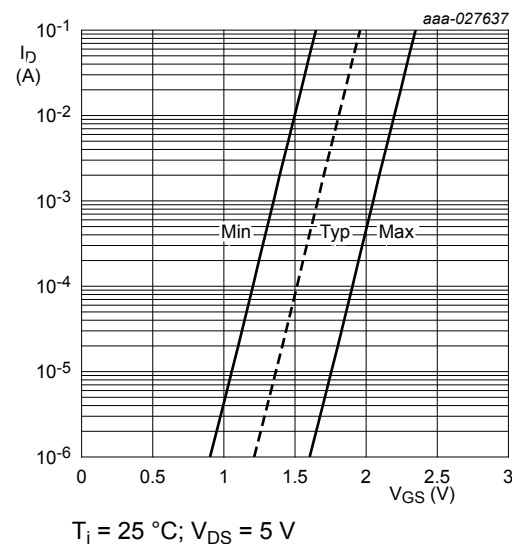


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

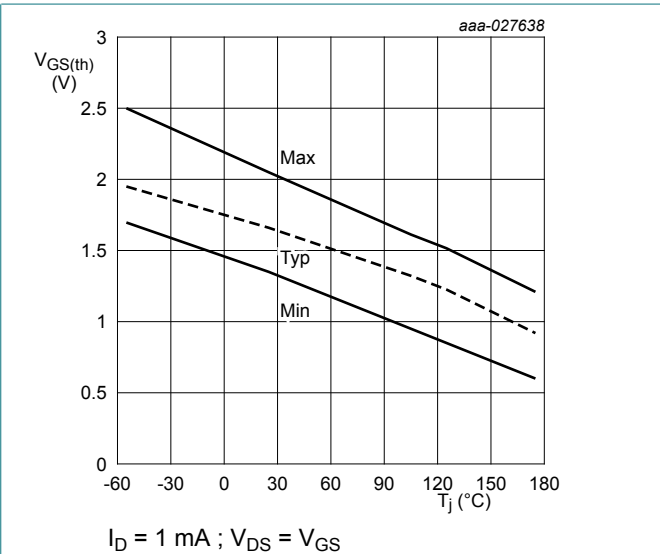


Fig. 9. Gate-source threshold voltage as a function of junction temperature

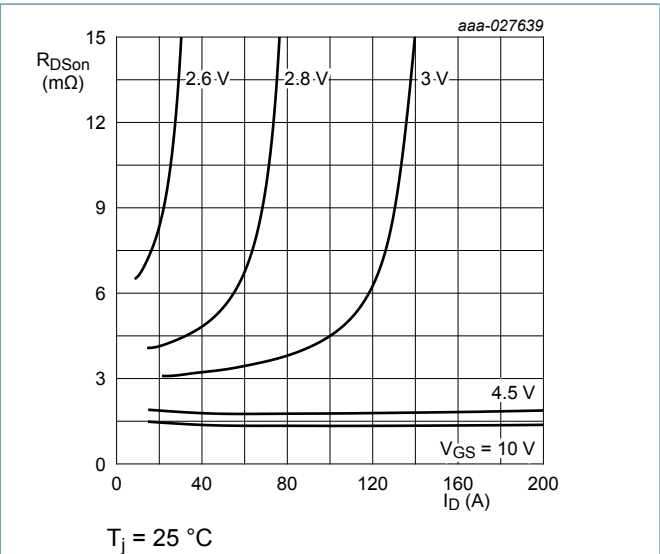


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

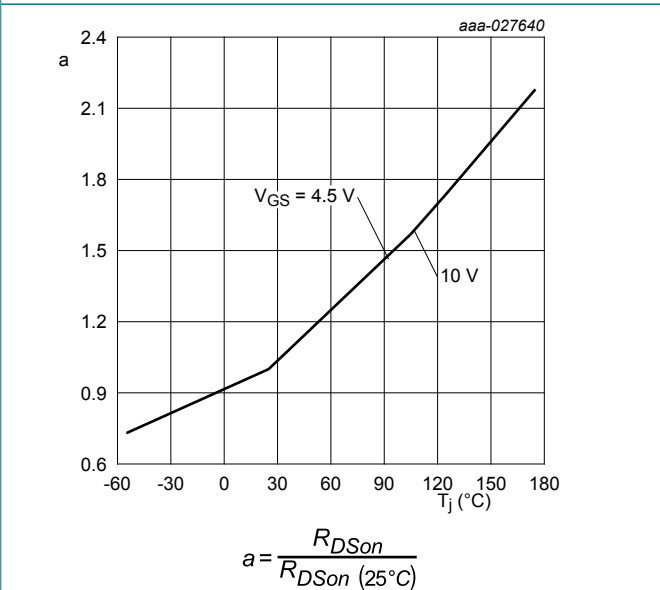


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

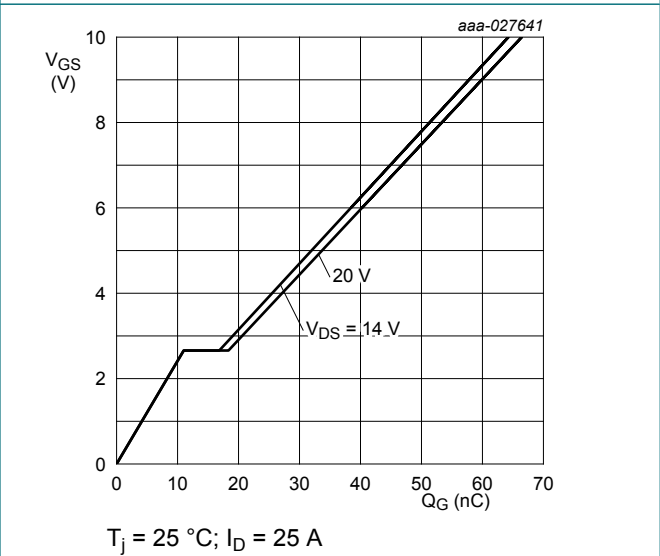


Fig. 12. Gate-source voltage as a function of gate charge; typical values

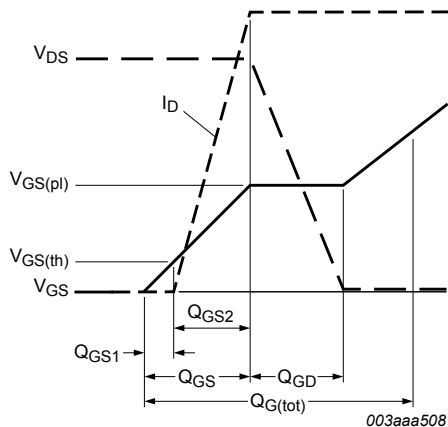
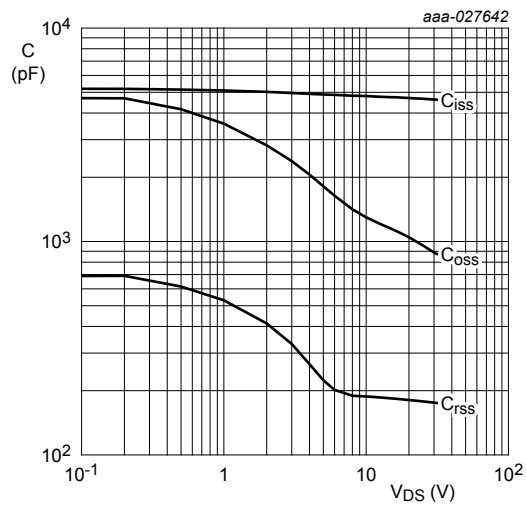
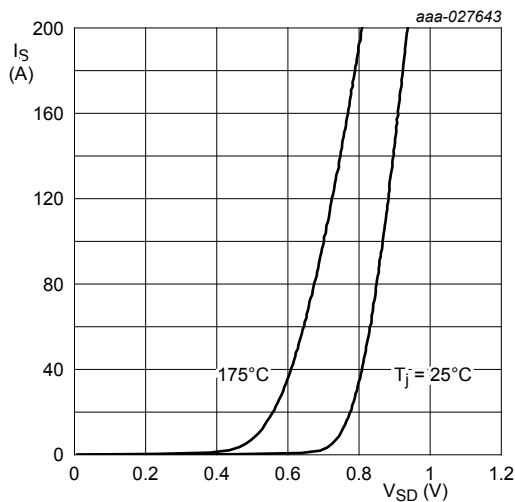


Fig. 13. Gate charge waveform definitions



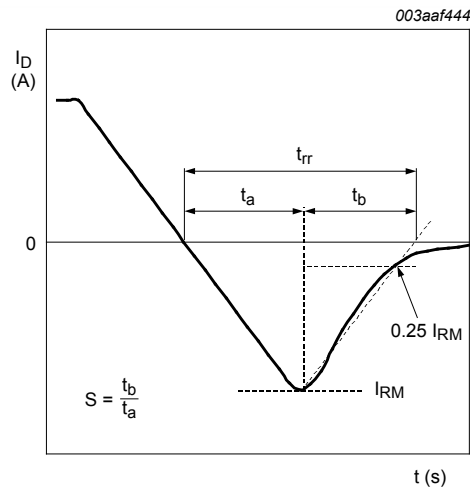
$V_{GS} = 0 \text{ V}$ ;  $f = 1 \text{ MHz}$

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0 \text{ V}$

Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values



$t_{rr} = t_a + t_b$

Fig. 16. Reverse recovery waveform definitions



11. Package outline

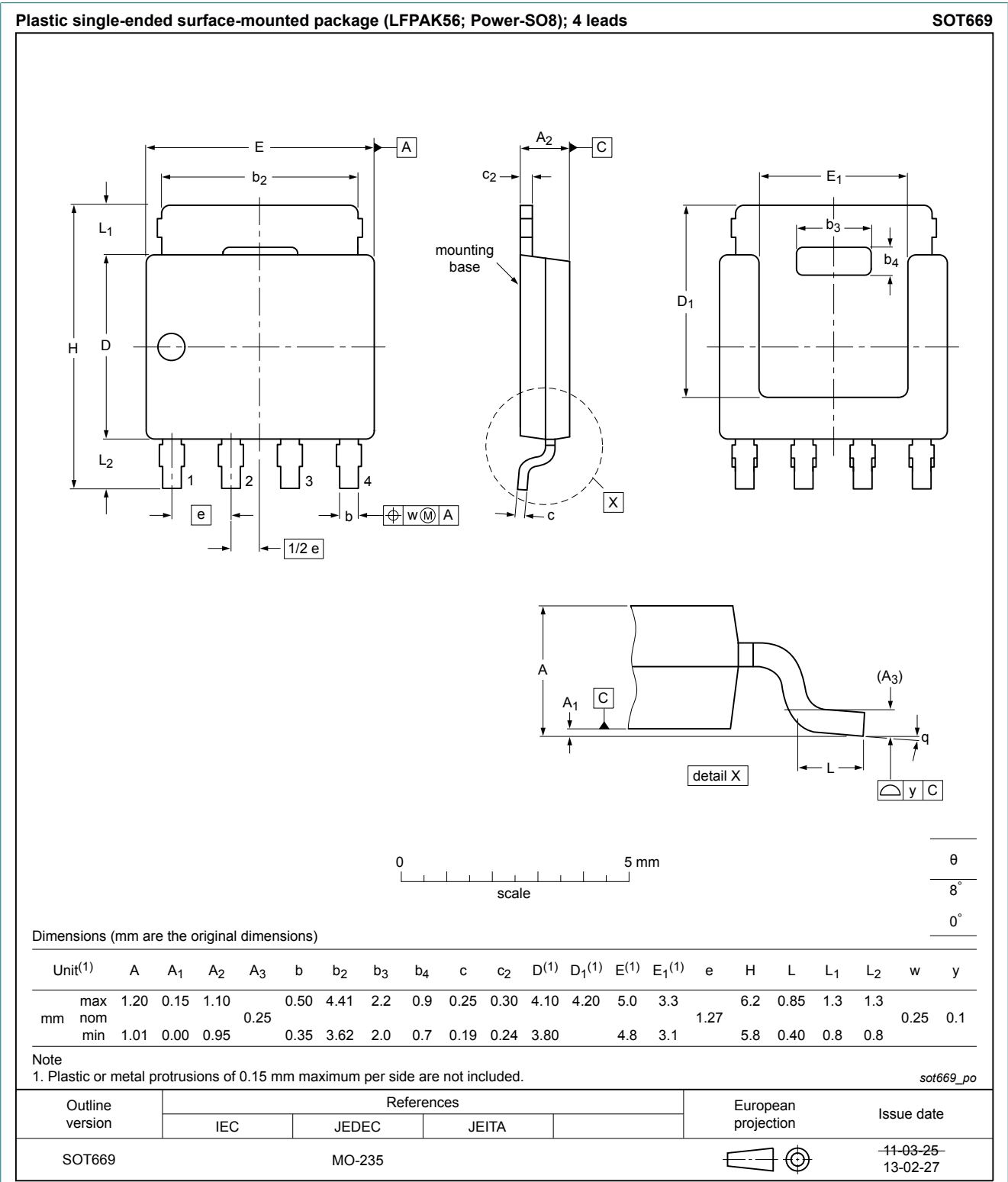


Fig. 17. Package outline LPAK56; Power-SO8 (SOT669)

## 12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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